

	Hits	Search Text	DBs
1	4	((substrate or wafer or device) same (semiconduct\$4 or stack or lamin\$4 or layer or coat\$4 or multilayer or silicide) same (cap\$4 or Si\$2N\$2 or (silicon near6 nitride)) same (photoresist or resist or (radiation near6 sensitive))) and ((photoresist or resist or photosensitive or (radiation near6 sensitive)) same pattern\$4 same (etch near4 sensit\$5) same (sputter\$4 or coat\$4 or deposit\$4) same (silicon or si))	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB
2	173	((substrate or wafer or device) same (semiconduct\$4 or silicide) same ((cap or Si\$2N\$2 or (silicon near6 nitride)) near8 (layer\$3 or coat\$4 or deposit\$4 or film)) same (photoresist or resist or (radiation near6 sensitive))) and ((photoresist or resist or photosensitive or (radiation near6 sensitive)) same pattern\$4 same (etch\$3 near4 resist\$5) same ((sputter\$4 or coat\$4 or deposit\$4) near16 (silicon or si))) and (etch\$4 same (cap\$3 or SiN or (silicon near6 nitride) or Si\$2N\$2) same anisotropic\$4)	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB
3	4	(etch\$4 near4 mask near6 (silicon or "Si")) and ((mask or pattern) near6 (sputter\$4) near4 (silicon or polysilicon or "Si") near6 (photoresist or resist) near5 (conformal\$4 or topside or top or sidewall or side))	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB

	Hits	Search Text	DBs
4	165	((substrate or wafer or device) same (semiconduct\$4 or silicide) same ((cap or Si\$2N\$2 or (silicon near6 nitride)) near8 (layer\$3 or coat\$4 or deposit\$4 or film)) same (photoresist or resist or (radiation near6 sensitive))) and ((photoresist or resist or photosensitive or (radiation near6 sensitive)) same pattern\$4 same (etch\$3 near4 resist\$5) same ((sputter\$4 or coat\$4 or deposit\$4) near8 (silicon or si))) and (etch\$4 same (cap\$3 or SiN or (silicon near6 nitride) or Si\$2N\$2) same anisotropic\$4)	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB
5	86	((substrate or wafer or device) same ((semiconduct\$4 or silicide) near6 (layer\$4 or deposit\$4 or coat\$4 or film)) same ((cap or Si\$2N\$2 or (silicon near6 nitride)) near8 (layer\$3 or coat\$4 or deposit\$4 or film)) same (photoresist or resist or (radiation near6 sensitive)) same pattern\$4) and ((photoresist or resist or photosensitive or (radiation near6 sensitive)) same pattern\$4 same (etch\$3 near4 resist\$5) same ((sputter\$4 or coat\$4 or deposit\$4) near8 (silicon or si))) and (etch\$4 same (cap\$3 or SiN or (silicon near6 nitride) or Si\$2N\$2) same anisotropic\$4 same (silicide or semiconduct\$4))	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB

	Hits	Search Text	DBs
6	67	((substrate or wafer or device) same ((semiconduct\$4 or silicide) near6 (layer\$4 or deposit\$4 or coat\$4 or film)) same ((cap or Si\$2N\$2 or (silicon near6 nitride)) near8 (layer\$3 or coat\$4 or deposit\$4 or film)) same (photoresist or resist or (radiation near6 sensitive)) same pattern\$4) and ((photoresist or resist or photosensitive or (radiation near6 sensitive)) same pattern\$4 same (etch\$3 near4 resist\$5) same ((sputter\$4 or coat\$4 or deposit\$4) near8 (silicon or si))) and (etch\$4 same (cap\$3 or SiN or (silicon near6 nitride) or Si\$2N\$2) same anisotropic\$4 same (silicide or semiconduct\$4)) and (((etch\$4 or pattern\$4) near6 mask) near9 (silicon or Si))	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB

	Hits	Search Text	DBs
7	6	((substrate or wafer or device) same (silicide near6 (layer\$4 or deposit\$4 or coat\$4 or film)) same ((cap or Si\$2N\$2 or (silicon near6 nitride)) near8 (layer\$3 or coat\$4 or deposit\$4 or film)) same (photoresist or resist or (radiation near6 sensitive)) same pattern\$4) and ((photoresist or resist or photosensitive or (radiation near6 sensitive)) same pattern\$4 same (etch\$3 near4 resist\$5) same ((sputter\$4 or coat\$4 or deposit\$4) near8 (silicon or si))) and (etch\$4 same (cap\$3 or SiN or (silicon near6 nitride) or Si\$2N\$2) same anisotropic\$4 same (silicide or semiconduct\$4)) and (((etch\$4 or pattern\$4) near4 mask) near4 (silicon or Si or polysilicon or polySi))	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB

	Hits	Search Text	DBs
8	10	((substrate or wafer or device) same ((semiconduct\$4 or silicide) near6 (layer\$4 or deposit\$4 or coat\$4 or film)) same ((cap or Si\$2N\$2 or (silicon near6 nitride)) near8 (layer\$3 or coat\$4 or deposit\$4 or film)) same (photoresist or resist or (radiation near6 sensitive)) same pattern\$4) and ((photoresist or resist or photosensitive or (radiation near6 sensitive)) near12 pattern\$4 near8 (etch\$3 near4 resist\$5) near14 ((sputter\$4 or coat\$4 or deposit\$4) near4 (silicon or si))) and (etch\$4 same (cap\$3 or SiN or (silicon near6 nitride) or Si\$2N\$2) same anisotropic\$4 same (silicide or semiconduct\$4)) and (((etch\$4 or pattern\$4) near6 mask) near4 (silicon or Si))	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB

	Hits	Search Text	DBs
9	0	((substrate or wafer or device) same ((semiconduct\$4 or silicide) near6 (layer\$4 or deposit\$4 or coat\$4 or film)) same ((cap or Si\$2N\$2 or (silicon near6 nitride)) near8 (layer\$3 or coat\$4 or deposit\$4 or film)) same ((photoresist or resist or (radiation near6 sensitive)) near12 pattern\$4 near9 etch near6 mask)) and ((photoresist or resist or photosensitive or (radiation near6 sensitive)) same pattern\$4 same (etch\$3 near4 resist\$5)) and (sputter\$4 near8 (silicon or si) near16 (resist or photoresist) near6 pattern\$3 near9 mask) and (etch\$4 same (cap\$3 or SiN or (silicon near6 nitride) or Si\$2N\$2) same anisotropic\$4 same (silicide or semiconduct\$4)) and (etch\$4 near6 mask near5 (silicon or Si)))	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB
10	6	((etch near6 resistant) near9 mask near6 (silicon or "Si")) and ((mask or pattern) near5 (resist or photoresist) near6 (sputter\$4 or coat\$4 or deposit\$4) near4 (silicon or polysilicon or "Si"))	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB
11	91	(etch\$4 near4 mask near6 (silicon or "Si")) and ((mask or pattern) near5 (resist or photoresist) near6 (sputter\$4) near4 (silicon or polysilicon or "Si"))	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB

	Hits	Search Text	DBs
12	43	(etch\$4 near4 mask near6 (silicon or "Si")) and ((mask or pattern) near6 (sputter\$4 or coat\$4 or deposit\$4) near4 (silicon or polysilicon or "Si") near6 (photoresist or resist) near5 (conformal\$4 or topside or top or sidewall or side))	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB
13	0	(etch\$4 near5 resist\$4 near4 mask near6 (silicon or "Si") near5 sputter\$4) and (pattern\$4 near6 (photoresist or resist) near5 (conformal\$4 or topside or top or sidewall or side) near5 (silicon or polysilicon or (polycrystalline near4 silicon)))	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB
14	0	(etch\$4 near5 resist\$4 near4 mask near6 (silicon or "Si") near5 sputter\$4) and ((photoresist or resist) near5 (conformal\$4 or topside or top or sidewall or side) near5 (silicon or polysilicon or (polycrystalline near4 silicon)))	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB
15	16	(etch\$4 near5 resist\$4 near4 mask near6 (silicon or "Si") near5 sputter\$4)	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB
16	2	((silicon or "Si") near5 sputter\$4 near6 (photoresist or resist) near4 (mask or pattern) near5 (conformal\$4 or sidewall or (vertical near4 side) or (top near4 surface) or (top near5 side)))	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB

	Hits	Search Text	DBs
17	2	((silicon or "Si" or polysilicon or (polycrystalline near4 silicon)) near5 (sputter\$4 or PVD or (physical near4 vapor)) near6 (photoresist or resist) near4 (mask or pattern) near5 (conformal\$4 or sidewall or side or (vertical near4 side) or (top near4 surface) or (top near5 side)))	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB
18	2	((silicon or "Si"). near5 (sputter\$4 or PVD or (physical near4 vapor)) near6 (photoresist or resist) near4 (mask or pattern) near5 (conformal\$4 or sidewall or side or (vertical near4 side) or (top near4 surface) or (top near5 side)))	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB
19	27	((silicon or "Si" or polysilicon or (polycrystalline near4 silicon)) near5 (sputter\$4 or PVD or (physical near4 vapor)) near6 (mask or pattern) near5 (conformal\$4 or sidewall or side or (vertical near4 side) or (top near4 surface) or (top near5 side)))	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB
20	27	S19 NOT S15	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB